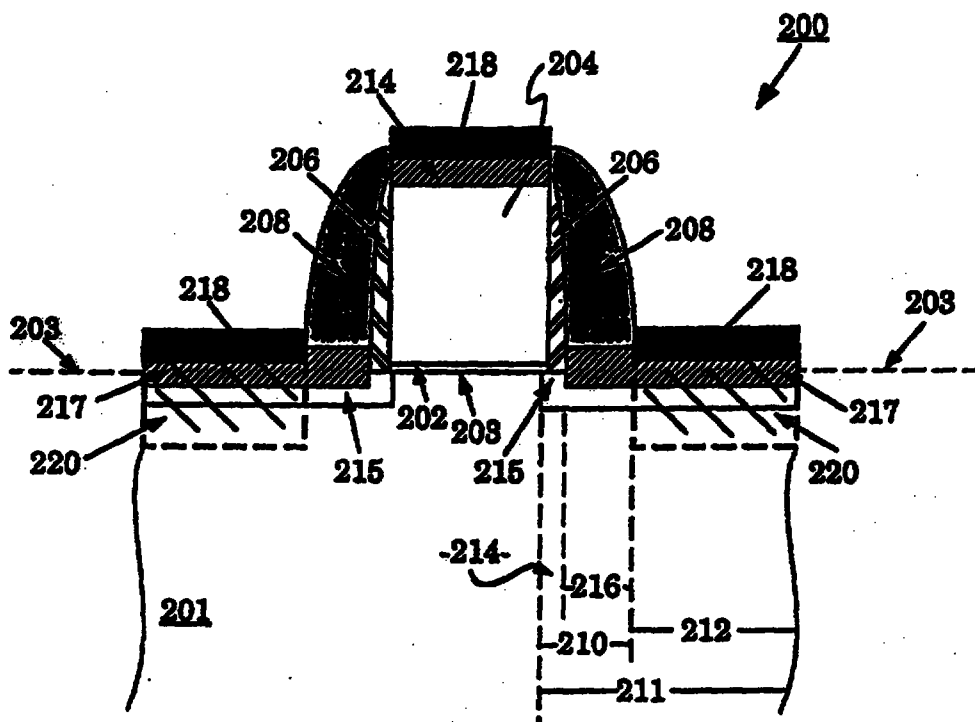


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(54) Title: NOVEL TRANSISTOR WITH ULTRA SHALLOW TIP AND METHOD OF FABRICATION



(57) Abstract

A novel transistor (200) with a low resistance ultra shallow tip region (214) and its method of fabrication. The novel transistor of the present invention has a source/drain extension or tip region (210) comprising an ultra shallow region (214) which extends beneath the gate electrode and a raised region (216).